

RJK03M5DNS

Silicon N Channel Power MOS FET Power Switching

R07DS0769EJ0110 Rev.1.10 May 29, 2012

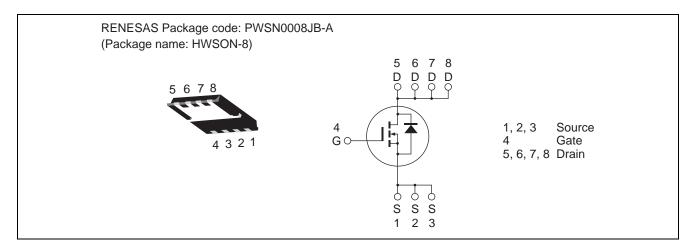
Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)} = 5.2 \text{ m}\Omega \text{ typ. (at } V_{GS} = 10 \text{ V})$

- Pb-free
- Halogen-free

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	25	A
Drain peak current	I _{D(pulse)} Note1	100	A
Body-drain diode reverse drain current	I _{DR}	25	A
Avalanche current	I _{AP} Note 2	10.5	A
Avalanche energy	E _{AS} Note 2	11	mJ
Channel dissipation	Pch Note3	15	W
Channel to case thermal impedance	θch-c Note3	8.3	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tch = 25°C, Rg \geq 50 Ω
- 3. Tc = 25°C

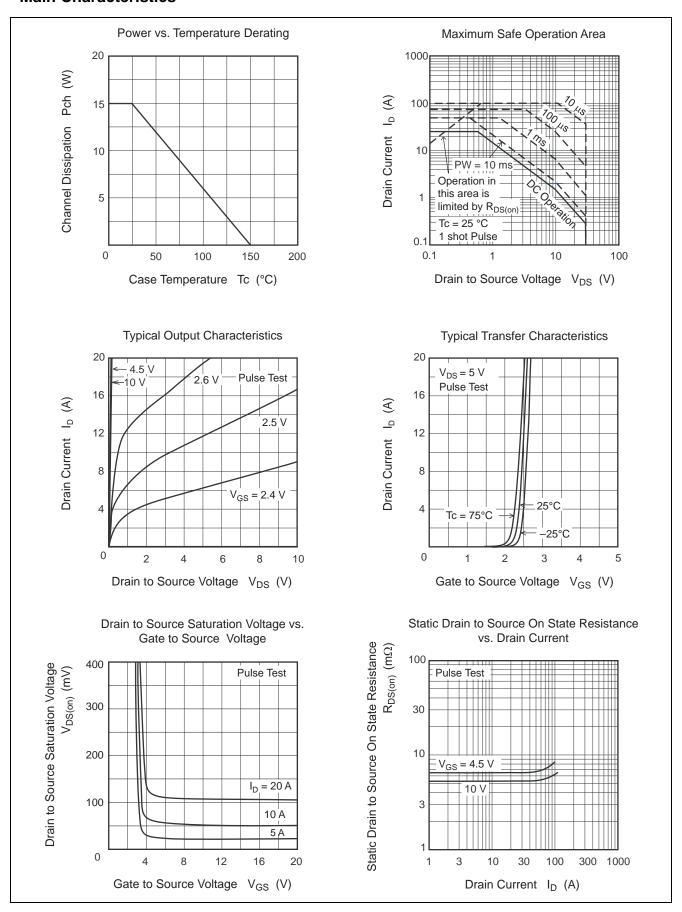
Electrical Characteristics

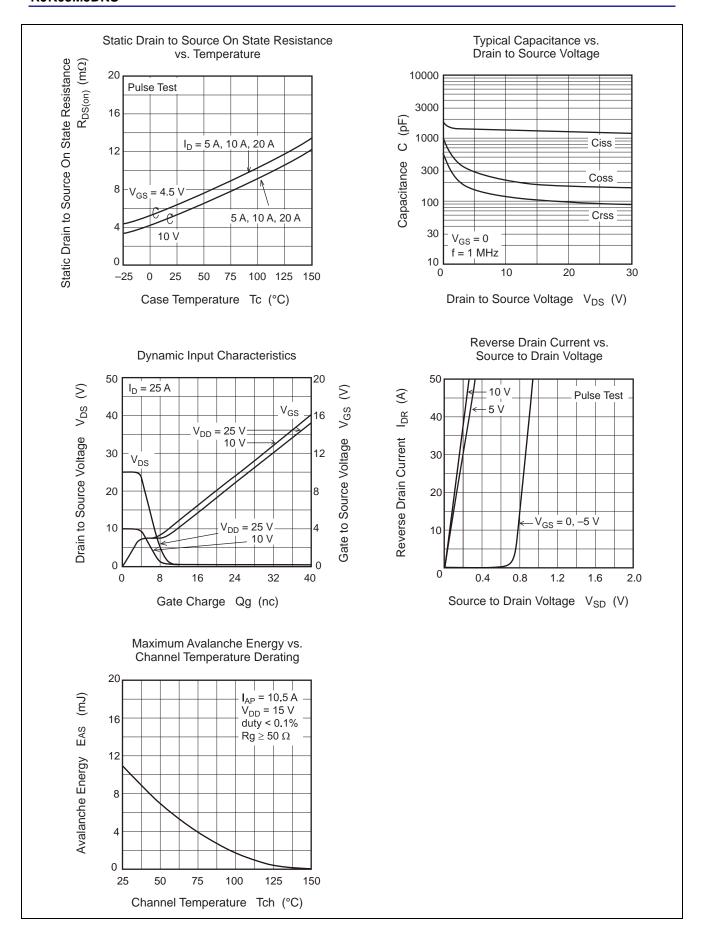
 $(Ta = 25^{\circ}C)$

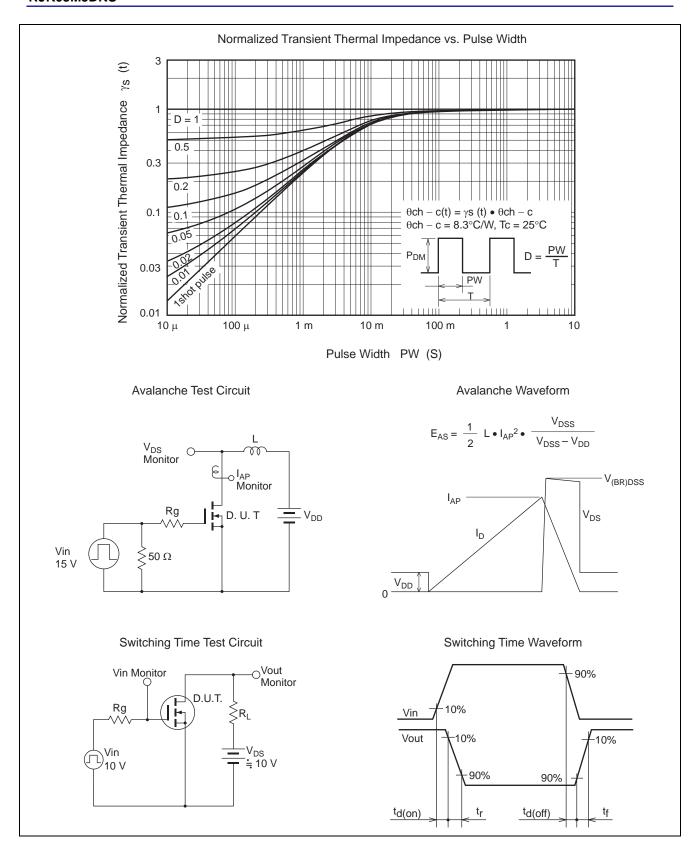
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I_{GSS}	_	_	± 0.5	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	1	_	1	μΑ	$V_{DS} = 24 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.2	_	2.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	5.2	6.3	mΩ	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R _{DS(on)}	_	6.4	8.4	mΩ	$I_D = 12.5 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y _{fs}	_	60	_	S	$I_D = 12.5 \text{ A}, V_{DS} = 5 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	1350	1890	рF	$V_{DS} = 10 \text{ V}$
Output capacitance	Coss	_	220	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss		120	_	pF	
Gate Resistance	Rg		1.4	2.8	Ω	
Total gate charge	Qg	_	10.4	_	nC	V _{DD} = 10 V V _{GS} = 4.5 V I _D = 25 A
Gate to source charge	Qgs	_	4.0	_	nC	
Gate to drain charge	Qgd	_	3.1	_	nC	
Turn-on delay time	t _{d(on)}	_	3.7	_	ns	$V_{GS} = 10 \text{ V}, I_D = 12.5 \text{ A}$
Rise time	t _r	_	3.0	_	ns	$V_{DD} \cong 10 \text{ V}$ $R_L = 0.8 \Omega$ $Rg = 4.7 \Omega$
Turn-off delay time	t _{d(off)}		21.7	_	ns	
Fall time	t _f		7.0	_	ns	
Body-drain diode forward voltage	V_{DF}		0.85	1.11	V	$I_F = 25 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body–drain diode reverse recovery	t _{rr}	_	8.8	_	ns	$I_F = 25 \text{ A}, V_{GS} = 0$
time						$di_F/dt = 500 \text{ A/ } \mu\text{s}$

Notes: 4. Pulse test

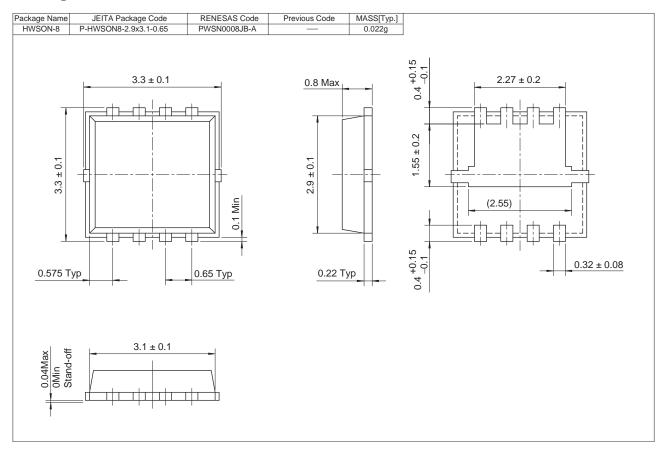
Main Characteristics







Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJK03M5DNS-00-J5	5000 pcs	Taping

Note: The symbol of 2nd "-" is occasionally presented as "#".

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